	DR. BABASAHEB AMBE	DKAR TECHNOLOGICA	AL UNIVERSITY	, LONERE	
	Regular & S	Supplementary Winter Ex	amination-2023		
	Course: B. Tech.Branch: Electronics EngineeringSemester			emester: VII	
Subject Code & Name: BTEXPE702E CMOS Design					
	Max Marks: 60 Date: 4/1/2024 Duration: 2:00			0 to 5:00 PM	
	 Instructions to the Students: All the questions are compulsory. The level of question/expected answer as per OBE or the Course Outcome (CO) on which the question is based is mentioned in () in front of the question. Use graph paper with proper scale for drawing layout. (CO) Marks 				
0.1	What do you mean by Photo	lithography? draw neat di	agrams and	4	12
x	explain CMOS n-well fabrication process in detail.				
Q.2				2	4
Ľ	equal rise and fall time.				
	Draw Layout for two input static CMOS OR gate (on graph paper with			1	8
	proper scale)				
Q. 3	Solve Any Two of the followi	ng.			
A)	What is Elmore delay model? What is the effect of interconnect on		2	6	
	parasitic on delay?				
B)	Implement logic function $Y = A\overline{B}(C + \overline{D})$ using Static CMOS logic			1	6
C)) Explain static and dynamic power in CMOS circuits. What is an			2	6
	activity factor?				
Q.4	Solve Any Two of the following.				
A)	Implement half adder circuit using static CMOS logic			2	6
B)	Write electrical, logical effort, parasitic effort for four input NOR gate.		2	6	
C)	Draw 6T SRAM cell and explain its working in detail			3	6
Q. 5	Solve Any Two of the following.				
A)	A combinational circuit is de	fined by following function	ns	1	6
		$(, C) = \sum_{m=1}^{\infty} m(1, 3, 6, 7)$			
$F_2(A, B, C) = \sum m(0, 2, 4, 5)$					
	Implement both functions using a PLA		_		
B)	Draw and explain the Voltage Transfer Characteristics for CM		s for CMOS	4	6
Â	inverter in detail.	·		-	
C)	Write a short note on CMOS	scaling		2	6